

QPD0007

DC-5GHz, 20 Watt, 48 Volt, GaN RF Transistor

Product Overview

05-25-2021

For the most up-to-date information, visit www.mouser.com or the supplier's website.

Description

The QPD0007 GaN RF Transistors are the single-path discrete GaN on SiC High-Electron-Mobility Transistors (HEMTs) that come in a DFN package. These GaN RF transistors are single-stage, unmatched transistors capable of delivering P_{3dB} output power of 20W at +48V operation. The QPD0007 transistors operate at DC to 5GHz frequency range and offer 73% drain efficiency at 3.5GHz. Applications include WCDMA/LTE, macrocell base station, microcell base station, general-purpose, small cell, active antenna, and 5G massive MIMO.



Features

- DC to 5GHz operating frequency range
- 48V operating drain voltage
- 20W maximum output power (P_{3dB}) at 3.6GHz
- 73% maximum drain efficiency at 3.5GHz
- 19dB efficiency-tuned back off gain at 3.5GHz
- 4.5mm x 4mm DFN package

Applications

- WCDMA/LTE
- Macrocell base station
- Microcell base station
- Small cell
- Active antenna
- 5G massive MIMO
- General-purpose applications

Mouser Part Number(s)

[View All Parts](#)

To learn more, visit <https://www.mouser.com/new/qorvo/qorvo-qpd0007-gan-rf-transistors/>